

1 ABSTRACT OF THE DISCLOSURE

2 The invention encompasses a method of forming a structure over
3 a semiconductor substrate. A silicon dioxide containing layer is formed
4 across at least some of the substrate. Nitrogen is formed within the
5 silicon dioxide containing layer. Substantially all of the nitrogen within
6 the silicon dioxide is at least 10Å above the substrate. After the
7 nitrogen is formed within the silicon dioxide layer, conductively doped
8 silicon is formed on the silicon dioxide layer. The invention
9 encompasses a method of forming a pair of transistors associated with
10 a semiconductor substrate. First and second regions of the substrate are
11 defined. A first oxide region is formed to cover the first region of the
12 substrate, and to not cover the second region of the substrate. Nitrogen
13 is formed within the first oxide region, and a first conductive layer is
14 formed over the first oxide region. After the first conductive layer is
15 formed, a second oxide region is formed over the second region of the
16 substrate. A second conductive layer is formed over the second oxide
17 region. The first conductive layer is patterned into a first transistor
18 gate, and the second conductive layer is patterned into a second
19 transistor gate. First source/drain regions are formed proximate the first
20 transistor gate, and the second source/drain regions are formed proximate
21 the second transistor gate. The invention also encompasses
22 semiconductor assemblies.

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